

Amendments to the Claims

Claim 1. (Currently Amended) A method of forming a resist pattern on a semiconductor substrate, comprising:

- forming a resist film on the semiconductor substrate;
- baking the resist film at a first temperature;
- exposing the resist film to light passing through a mask after baking the resist film at the first temperature;
- baking the resist film at a second temperature after exposing the resist film to the light, wherein the second temperature is different from the first temperature;
- supplying a developing solution on the resist film to remove the resist film, wherein a portion of the resist film remains on the semiconductor substrate; and
- rinsing the developing solution from the portion of the resist film by a rinsing liquid to which ultrasonic vibration is applied ~~wherein the ultrasonic vibration ranges from 40 kHz to 50Khz.~~

Claims 2-5. (Canceled)

Claim 6. (Previously Presented) The method according to claim 1, wherein the developing solution is an alkaline developing solution.

Claim 7. (Previously Presented) The method according to claim 6, wherein the alkaline developing solution includes tetramethylammonium hydroxide.

Claim 8-9. (Canceled)

Claim 10. (Currently Amended) The method according to claim 9 1, wherein the second temperature is lower than the first temperature.

Claim 11. (Currently Amended) A The method according to claim 1 of forming a resist pattern on a semiconductor substrate, further comprising:

forming a resist film on the semiconductor substrate;

baking the resist film at a first temperature;

irradiating the resist film with an electron beam using an electron beam lithography technique ~~before supplying the developing solution on the resist film~~ after baking the resist film at the first temperature;

baking the resist film at a second temperature after irradiating the resist film with the electron beam, wherein the second temperature is different from the first temperature;

supplying a developing solution on the resist film to remove the resist film, wherein a portion of the resist film remains on the semiconductor substrate; and

rinsing the developing solution from the portion of the resist film by a rinsing liquid to which ultrasonic vibration is applied.

Claim 12. (Canceled)

Claim 13. (Currently Amended) The method according to claim ~~12~~ 11, wherein the second temperature is lower than the first temperature.

Claim 14. (Canceled)

Claim 15. (Previously Presented) The method according to claim 1, wherein the ultrasonic vibration is applied to the developing solution.

Claim 16. (Previously Presented) The method according to claim 1, wherein the rinsing liquid is pure water.

Claim 17. (Currently Amended) A method for fabricating a semiconductor device, comprising:

preparing a semiconductor substrate;

forming a resist film on the semiconductor substrate;

baking the resist film at a first temperature;

exposing the resist film to light passing through a mask after baking the resist film at the first temperature;

baking the resist film at a second temperature after exposing the resist film to the light, wherein the second temperature is different from the first temperature;

supplying a developing solution on the resist film for patterning the resist film, whereby a patterned resist film is formed on the semiconductor substrate;

providing a rinsing liquid on the semiconductor substrate on which the patterned resist film is formed; and

applying ultrasonic vibration to the rinsing liquid ~~wherein the ultrasonic vibration ranges from 40 kHz to 50Khz.~~

Claim 18. (Canceled)

Claim 19. (Previously Presented) The method according to claim 17, wherein the developing solution is an alkaline developing solution.

Claim 20. (Previously Presented) The method according to claim 19, wherein the alkaline developing solution includes tetramethylammonium hydroxide.

Claim 21-22. (Canceled)

Claim 23. (Currently Amended) The method according to claim ~~22~~ 17, wherein the second temperature is lower than the first temperature.

Claim 24. (Currently Amended) A ~~The method according to claim 17~~ for fabricating a semiconductor device, further comprising:

preparing a semiconductor substrate;

forming a resist film on the semiconductor substrate;

baking the resist film at a first temperature;

irradiating the resist film with an electron beam using an electron beam lithography technique ~~before supplying the developing solution on the resist film~~ after baking the resist film at the first temperature;

baking the resist film at a second temperature after irradiating the resist film with the electron beam, wherein the second temperature is different from the first temperature;

supplying a developing solution on the resist film for patterning the resist film, whereby a patterned resist film is formed on the semiconductor substrate;

providing a rinsing liquid on the semiconductor substrate on which the patterned resist film is formed; and

applying ultrasonic vibration to the rinsing liquid.

Claim 25. (Canceled)

Claim 26. (Currently Amended) The method according to claim 25 24, wherein the second temperature is lower than the first temperature.

Claim 27. (Canceled)

Claim 28. (Previously Presented) The method according to claim 17, wherein the ultrasonic vibration is applied to the developing solution.

Claim 29. (Previously Presented) The method according to claim 17, wherein the rinsing liquid is pure water.

Claim 30. (Canceled)

Claim 31. (Currently Amended) A method of forming a resist pattern on a substrate, comprising:

forming a resist film on the substrate;

baking the resist film at a first temperature;

exposing the resist film to light passing through a mask after baking the resist film at the first temperature;

baking the resist film at a second temperature after exposing the resist film to the light, wherein the second temperature is different from the first temperature;

supplying a developing solution onto the resist film;

providing a rinsing liquid onto the substrate so as to cover the resist film; and

applying ultrasonic vibration to the rinsing liquid to rinse the developing solution from the resist film submerged in the rinsing liquid ~~wherein the ultrasonic vibration ranges from 40 kHz to 50Khz.~~

Claim 32. (Currently Amended) A method of forming a resist pattern on a substrate, comprising:

forming a resist film on the substrate;

baking the resist film at a first temperature;

exposing the resist film to light passing through a mask after baking the resist film at the first temperature;

baking the resist film at a second temperature after exposing the resist film to the light, wherein the second temperature is different from the first temperature;

supplying a developing solution onto the resist film;

supplying the resist film formed on the substrate with a rinsing liquid; and

applying ultrasonic vibration to the rinsing liquid to rinse the developing solution from the resist film submerged in the rinsing liquid ~~wherein the ultrasonic vibration ranges from 40 kHz to 50Khz.~~

Claim 33. (New) The method according to claim 11, wherein the ultrasonic vibration is applied to the developing solution.

Claim 34. (New) The method according to claim 11, wherein the rinsing liquid is pure water.

Claim 35. (New) The method according to claim 24, wherein the ultrasonic vibration is applied to the developing solution.

Claim 36. (New) The method according to claim 24, wherein the rinsing liquid is pure water.

Claim 37. (New) A method of forming a resist pattern on a substrate, comprising:
forming a resist film on the substrate;
baking the resist film at a first temperature;
irradiating the resist film with an electron beam using an electron beam lithography technique after baking the resist film at the first temperature;
baking the resist film at a second temperature after irradiating the resist film with the electron beam, wherein the second temperature is different from the first temperature;
supplying a developing solution onto the resist film;
providing a rinsing liquid onto the substrate so as to cover the resist film; and
applying ultrasonic vibration to the rinsing liquid to rinse the developing solution from the resist film submerged in the rinsing liquid.

Claim 38. (New) A method of forming a resist pattern on a substrate, comprising:
forming a resist film on the substrate;
baking the resist film at a first temperature;
irradiating the resist film with an electron beam using an electron beam lithography technique after baking the resist film at the first temperature;
baking the resist film at a second temperature after irradiating the resist film with the electron beam, wherein the second temperature is different from the first temperature;
supplying a developing solution onto the resist film;
supplying the resist film formed on the substrate with a rinsing liquid; and
applying ultrasonic vibration to the rinsing liquid to rinse the developing solution from the resist film submerged in the rinsing liquid.

Claim 39. (New) The method according to claim 17, wherein the ultrasonic vibration ranges from 40 kHz to 50 kHz.

Claim 40. (New) The method of Claim 1, wherein the ultrasonic vibration ranges from 40 kHz to 50 kHz.